

Silicon NPN Power Transistors

2N3237

DESCRIPTION

- With TO-3 package
- Excellent safe operating area
- Low collector saturation voltage

APPLICATIONS

- For power amplifier and switching circuits applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

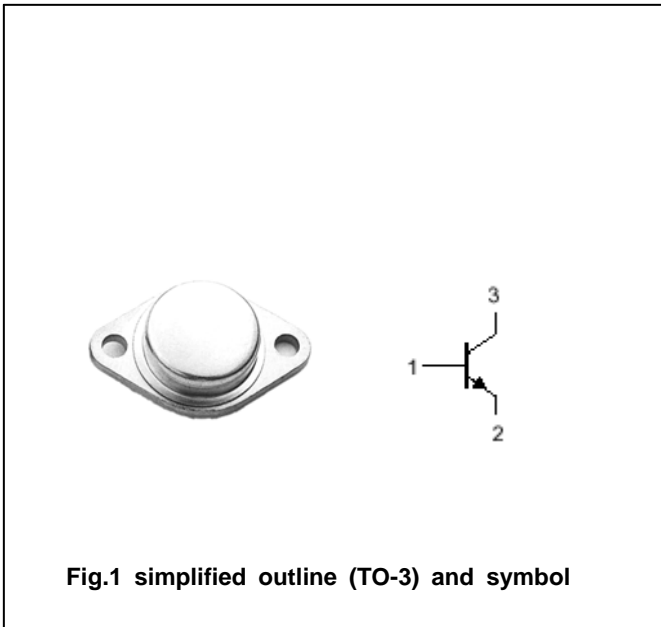


Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	90	V
V _{CEO}	Collector-emitter voltage	Open base	90	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		20	A
I _B	Base current		7.5	A
P _D	Total power dissipation	T _C =25°C	200	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	0.875	°C/W

Silicon NPN Power Transistors

2N3237

CHARACTERISTICS

 $T_j=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=0.2A ; I_B=0$	90			V
$V_{CE(sat)-1}$	Collector-emitter saturation voltage	$I_C=10A ; I_B=1.0A$			1.4	V
$V_{CE(sat)-2}$	Collector-emitter saturation voltage	$I_C=20A ; I_B=4.0A$			4.0	V
$V_{BE(on)}$	Base-emitter on voltage	$I_C=10A ; V_{CE}=4V$			2.2	V
I_{CEO}	Collector cut-off current	$V_{CE}=45V ; I_B=0$			1.0	mA
I_{CBO}	Collector cut-off current	$V_{CB}=90V ; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			0.1	mA
h_{FE-1}	DC current gain	$I_C=1A ; V_{CE}=4V$	40			
h_{FE-2}	DC current gain	$I_C=10A ; V_{CE}=4V$	15		60	
h_{FE-3}	DC current gain	$I_C=20A ; V_{CE}=4V$	5			

PACKAGE OUTLINE

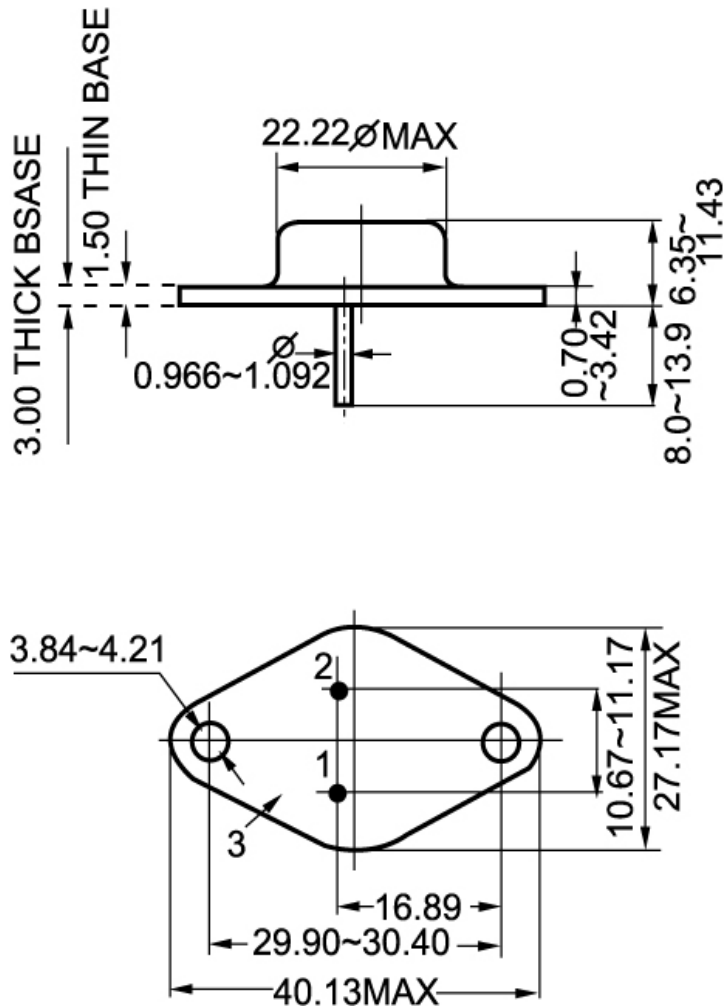


Fig.2 outline dimensions (unindicated tolerance: ±0.1mm)